

Data Sheet January 2000 File Number 3695.2

15A, 1200V Ultrafast Dual Diode

The RURG15120CC is an ultrafast dual diode with soft recovery characteristics (t_{rr} < 100ns). It has low forward voltage drop and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

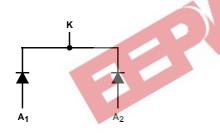
Formerly developmental type TA49097.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RURG15120CC	TO-247	URG15120C

NOTE: When ordering, use the entire part number.

Symbol



Features

Ultrafast with Soft Recovery	<100ns
Operating Temperature	.175 ⁰ C
Reverse Voltage	.1200V

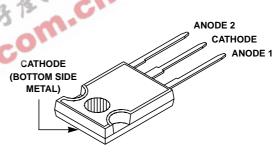
- Avalanche Energy Rated
- · Planar Construction

Applications

- · Switching Power Supplies
- · Power Switching Circuits
- General Purpose

Packaging

JEDEC STYLE TO-247



RURG15120CC

UNITS

Absolute Maximum Ratings (Per Leg) T_C = 25°C, Unless Otherwise Specified

Peak Repetitive Reverse VoltageV _{RRM}	1200	V
Working Peak Reverse Voltage	1200	V
DC Blocking VoltageV _R	1200	V
Average Rectified Forward Current $I_{F(AV)}$ ($T_C = 140^{\circ}C$)	15	Α
Repetitive Peak Surge CurrentI _{FRM} (Square Wave, 20kHz)	30	Α
Nonrepetitive Peak Surge Current	200	Α
Maximum Power Dissipation	100	W
Avalanche Energy (See Figures 10 and 11)	20	mJ
Operating and Storage Temperature	-65 to 175	οС

RURG15120CC

Electrical Specifications (Per Leg) $T_C = 25^{\circ}C$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS		
V _F	I _F = 15A	-	-	2.1	V		
	I _F = 15A, T _C = 150 ^o C	-	-	1.9	V		
I _R	V _R = 1200V	-	-	100	μА		
	V _R = 1200V, T _C = 150°C	-	-	500	μА		
t _{rr}	I _F = 1A, dI _F /dt = 100A/μs	-	-	100	ns		
	I _F = 15A, dI _F /dt = 100A/μs	-	-	130	ns		
ta	I _F = 15A, dI _F /dt = 100A/μs	-	65	-	ns		
t _b	I _F = 15A, dI _F /dt = 100A/μs	-	40	-	ns		
Q _{RR}	I _F = 15A, dI _F /dt = 100A/μs	-	400	-	nC		
СЈ	V _R = 10V, I _F = 0A	-	56	-	pF		
$R_{ heta JC}$		-	-	1.5	°C/W		
I _R = Instantane	eous forward voltage (pw = 300μs, D = 2%). eous reverse current. ecovery time (See Figure 9), summation of t _a + t _b .	** 为节	n peak I _{RM} through				
t _a = Time to reach peak reverse current (See Figure 9).							
$t_b = Time from$	peak $I_{\mbox{\scriptsize RM}}$ to projected zero crossing of $I_{\mbox{\scriptsize RM}}$ based on	a straight line fron	n peak I _{RM} through	h 25% of I $_{RM}$ (Se	ee Figure 9).		
Q _{RR} = Reverse re	ecovery charge.						

DEFINITIONS

C_J = Junction capacitance.

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

Typical Performance Curves

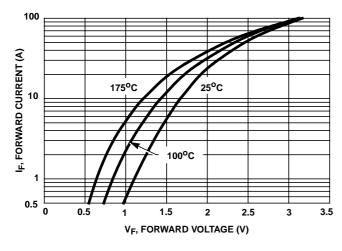


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

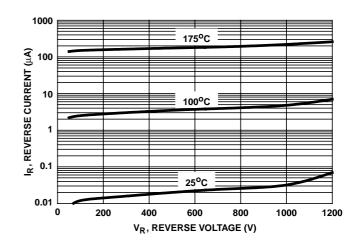


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

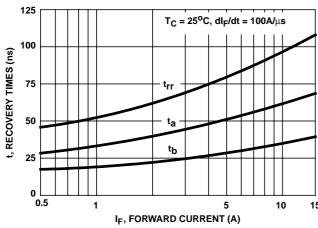


FIGURE 3. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

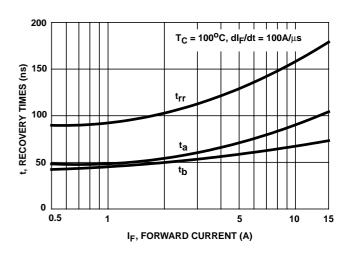


FIGURE 4. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

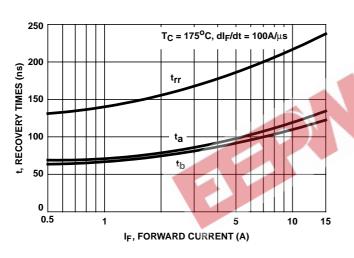


FIGURE 5. t_{rr} , t_a and t_b curves vs forward current

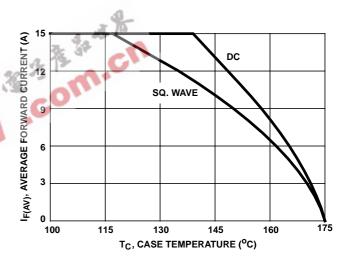


FIGURE 6. CURRENT DERATING CURVE

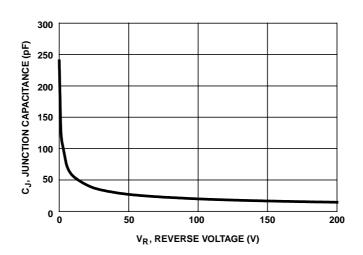


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

RURG15120CC

Test Circuits and Waveforms

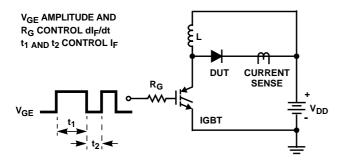


FIGURE 8. t_{rr} TEST CIRCUIT

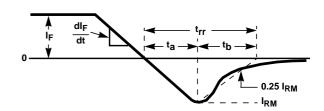


FIGURE 9. t_{rr} WAVEFORMS AND DEFINITIONS

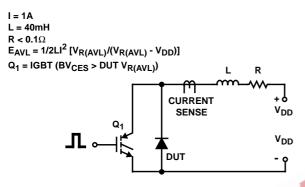


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

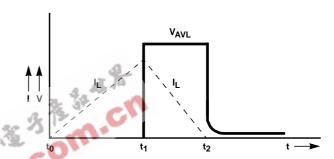


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

All Intersil semiconductor products are manufactured, assembled and tested under ISO9000 quality systems certification.

Intersil semiconductor products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see web site www.intersil.com